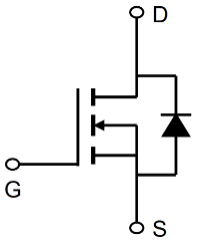
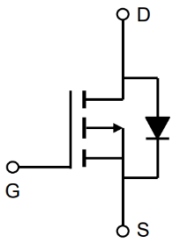
AP15G03NF

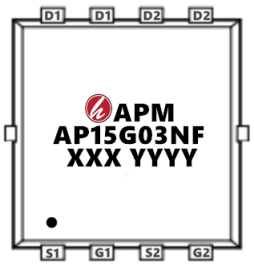
30V N+P-Channel Enhancement Mode MOSFET

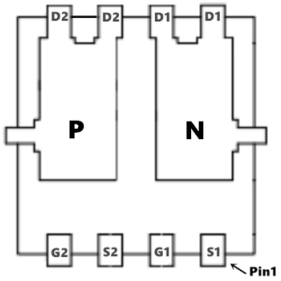
Description

The AP15G03NF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.









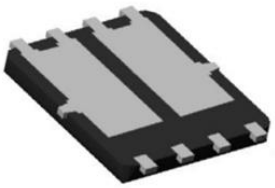
General Features

V_{DS} = 30V I_D =18A

$R_{DS(ON)}$ < 22mΩ @ V_{GS}=10V (Type：15mΩ)

V_{DS} = -30V I_D =-15A

$R_{DS(ON)}$ < 32mΩ @ V_{GS}=-10V (Type：25mΩ)



Application

Wireless charging

Boost driver

Brushless motor

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP15G03NF	PDFN5*6-8L	AP15G03NF XXX YYYY	5000

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating		Units
		N-Ch	P-Ch	
VDS	Drain-Source Voltage	30	-30	V
VGS	Gate-Source Voltage	±20	±20	V
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	18	-15	A
I_D@T_A=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	10	-8	A
IDM	Pulsed Drain Current[2]	52	-45	A
EAS	Single Pulse Avalanche Energy[3]	22	45	mJ
IAS	Avalanche Current	21	-30	A
P_D@T_A=25℃	Total Power Dissipation[4]	18	18	W
TSTG	Storage Temperature Range	-55 to 150	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	-55 to 150	℃
$R_{\theta}JA$	Thermal Resistance Junction-Ambient [1]	55		℃/W
$R_{\theta}JA$	Thermal Resistance Junction-Ambient[1],(t<=10sec)	5		℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	32.5	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=10A	---	15	22	mΩ
		V_{GS}=4.5V , I_D=5A	---	20	30	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.0	1.6	2.5	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=24V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=10A	---	16	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	2.5	5	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=20V , V_{GS}=4.5V , I_D=10A	---	7.2	---	nC
Q_{gs}	Gate-Source Charge		---	1.4	---	
Q_{gd}	Gate-Drain Charge		---	2.2	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=15V , V_{GS}=10V , R_G=3.3Ω, I_D=5A	---	4.1	---	ns
T_r	Rise Time		---	9.8	---	
$T_{d(off)}$	Turn-Off Delay Time		---	15.5	---	
T_f	Fall Time		---	6.0	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	572	---	pF
C_{oss}	Output Capacitance		---	81	---	
C_{rss}	Reverse Transfer Capacitance		---	65	---	
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	10	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V

Note :

1、The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

2、The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3、The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=10A

4、The power dissipation is limited by 150℃ junction temperature

5、The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Electrical Characteristics (T_C=25℃unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-30	-33	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-7A	---	25	32	mΩ
		V_{GS}=-4.5V , I_D=-5A	---	37	54	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.0	---	-2.5	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-24V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=-24V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-5V , I_D=-7A	---	15	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz		15	30	
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-20V , V_{GS}=-4.5V , I_D=-7A	---	9.8	---	nC
Q_{gs}	Gate-Source Charge		---	2.2	---	
Q_{gd}	Gate-Drain Charge		---	3.4	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-15V , V_{GS}=-10V , R_G=3.3 , I_D=-5A	---	16.4	---	ns
T_r	Rise Time		---	20.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	55	---	
T_f	Fall Time		---	10	---	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	930	---	pF
C_{oss}	Output Capacitance		---	148	---	
C_{rss}	Reverse Transfer Capacitance		---	115	---	
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	-8	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1.2	V

Note :

1、The data tested by surface mo unted on a 1 inch^2 FR-4 board with 2OZ copper.

2、The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3、The EAS data shows Max. rating . The test condition is V^{DD}=-25V,VGS=-10V,L=0.1mH,I^{AS}=-10A

4、The power dissipation is limited by 150℃ junction temperature

5 、The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

N-Typical Characteristics

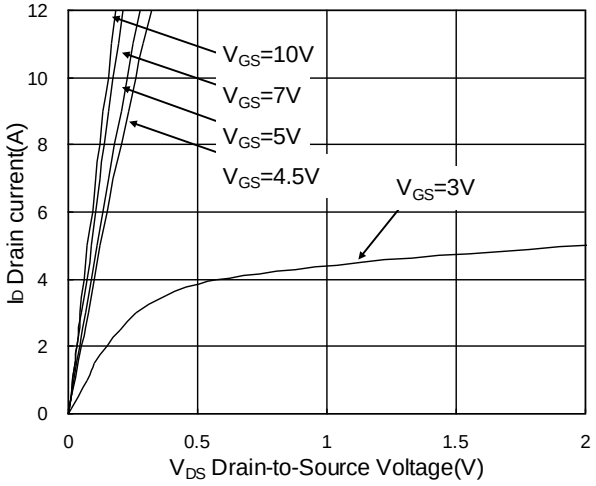


Fig.1 Typical Output Characteristics

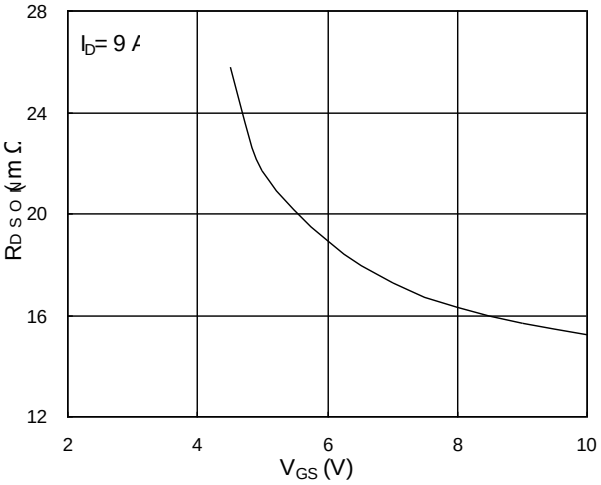


Fig.2 On-Resistance v.s Gate-Source

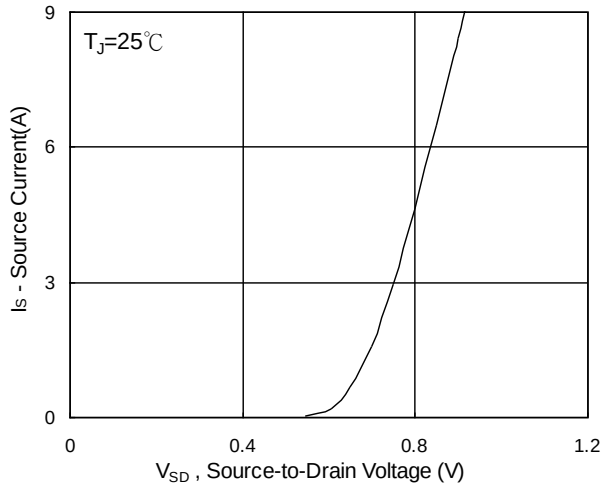


Fig.3 Forward Characteristics Of Reverse

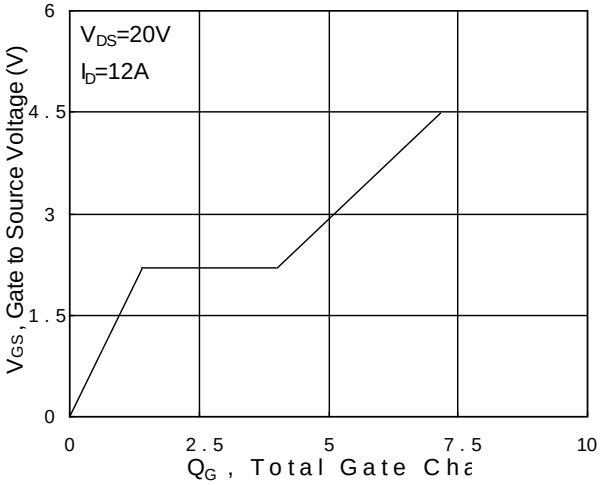


Fig.4 Gate-Charge characteristics

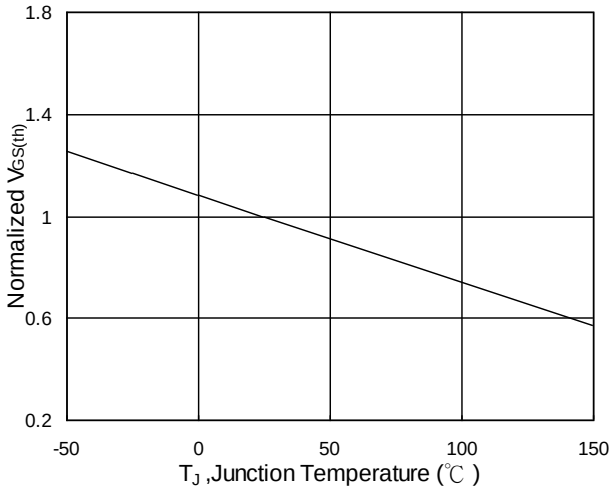


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

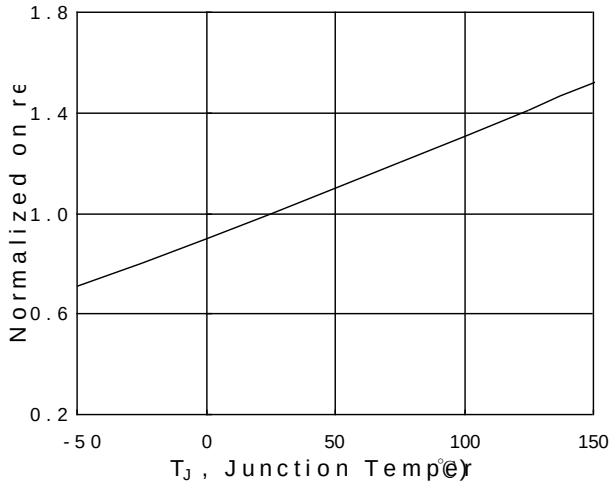


Fig.6 Normalized R_{DSON} v.s T_J

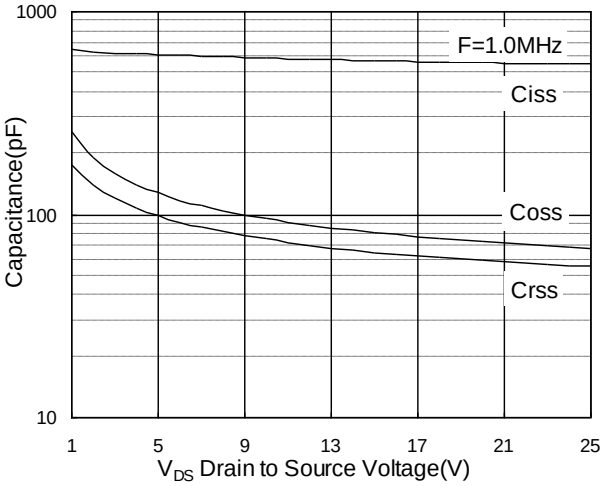


Fig.7 Capacitance

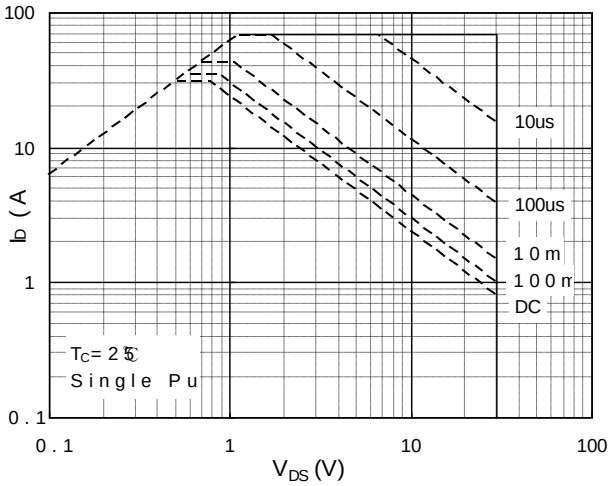


Fig.8 Safe Operating Area

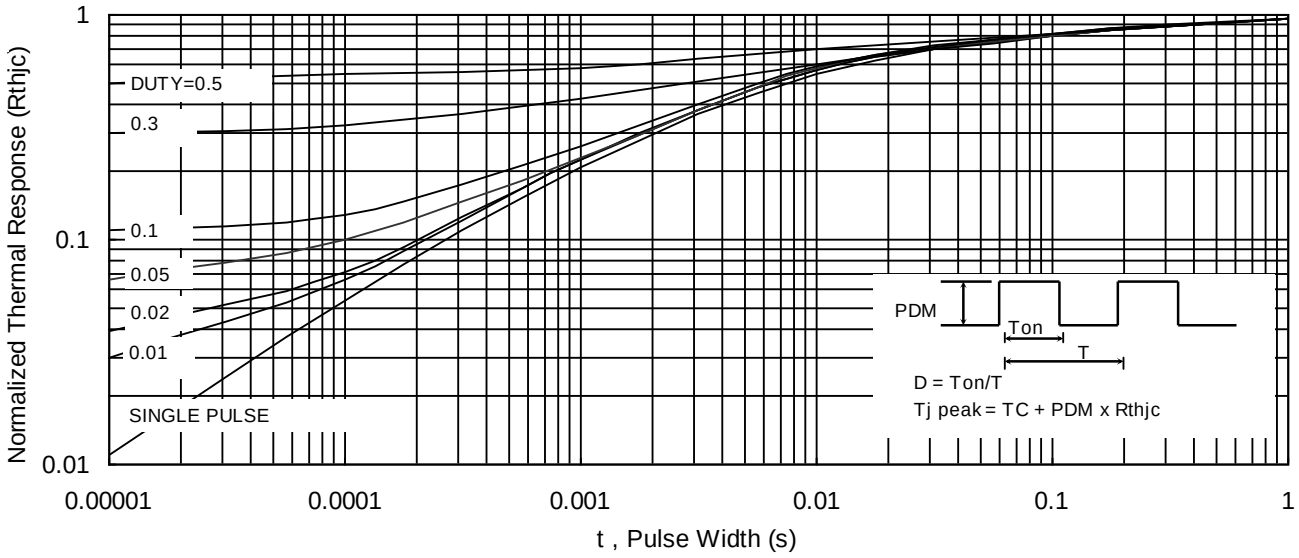


Fig.9 Normalized Maximum Transient Thermal Impedance

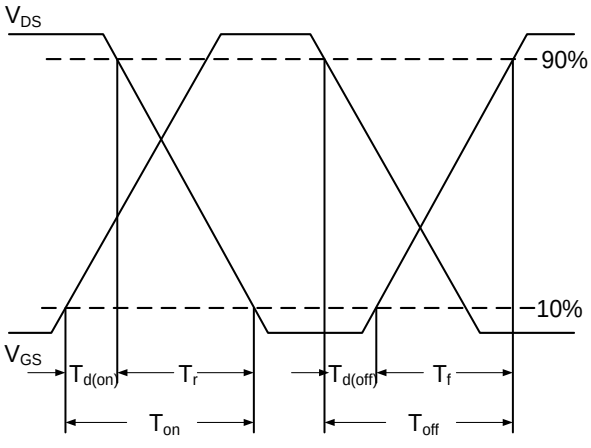


Fig.10 Switching Time Waveform

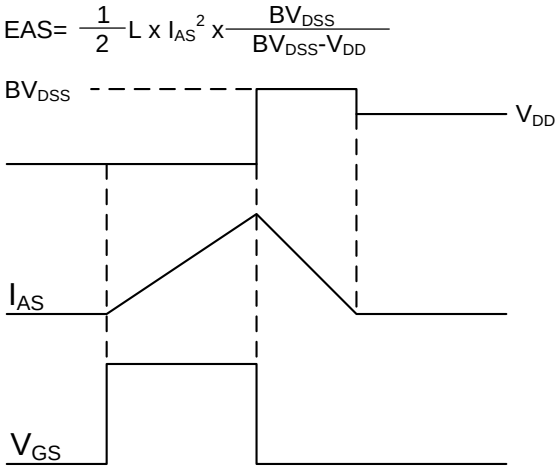


Fig.11 Unclamped Inductive Waveform

P-Typical Characteristics

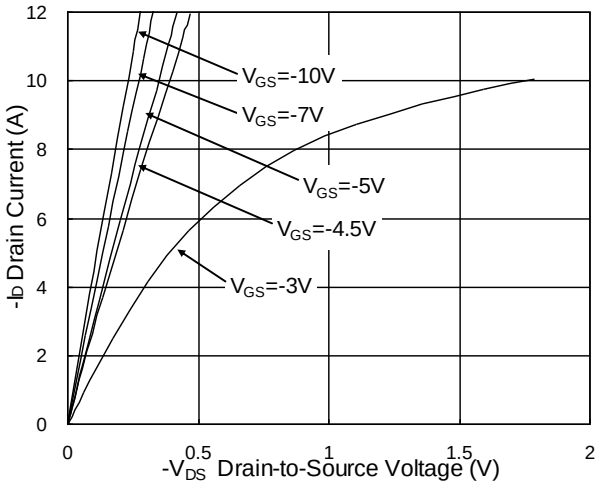


Fig.1 Typical Output Characteristics

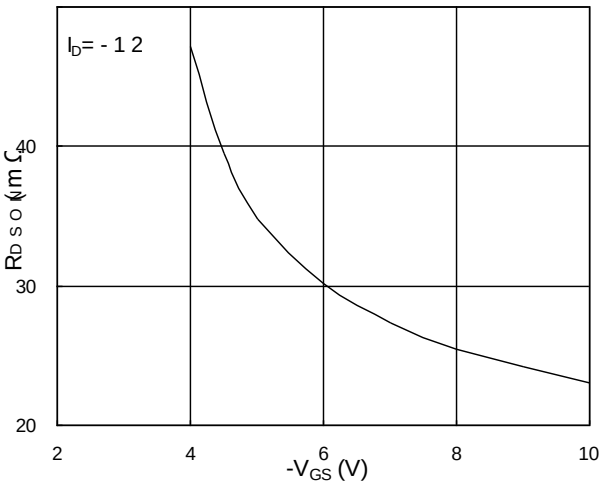


Fig.2 On-Resistance v.s Gate-Source

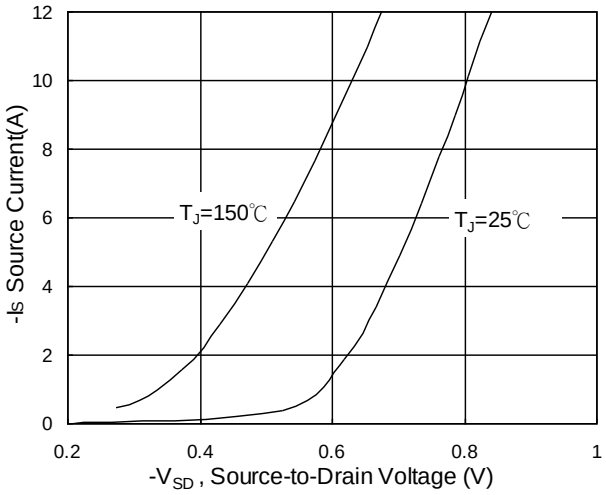


Fig.3 Forward Characteristics Of Reverse

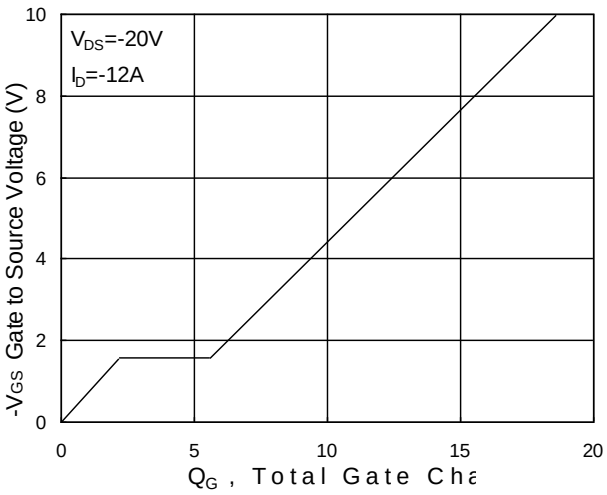


Fig.4 Gate-Charge Characteristics

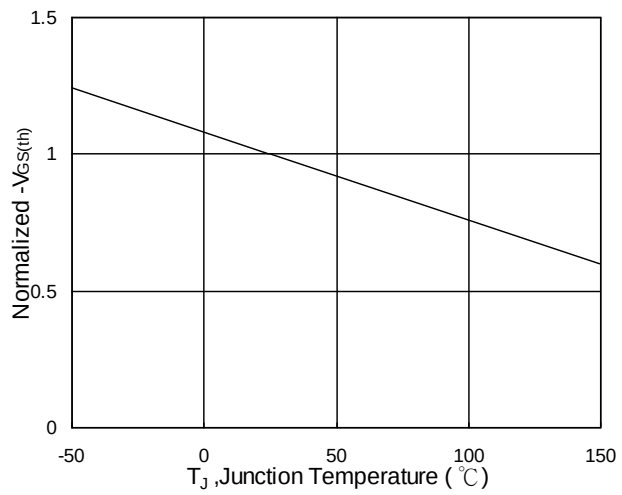


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

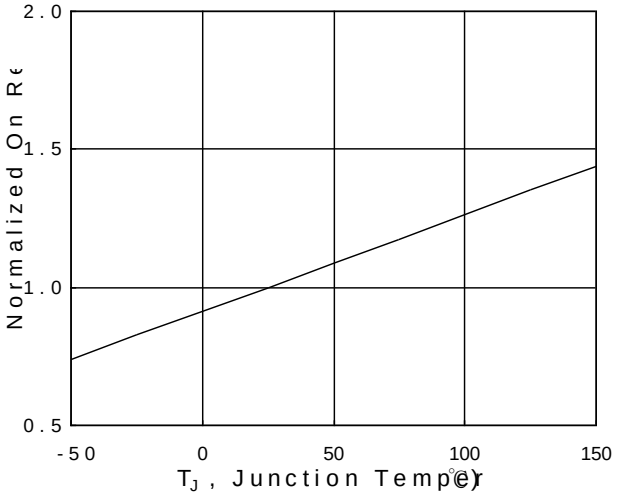


Fig.6 Normalized R_{DSON} v.s T_J

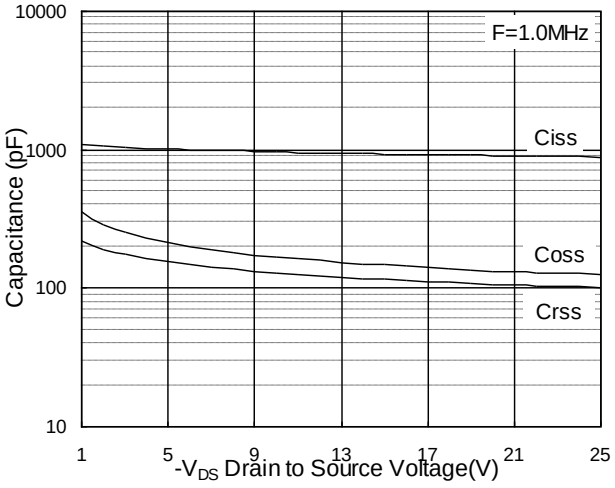


Fig.7 Capacitance

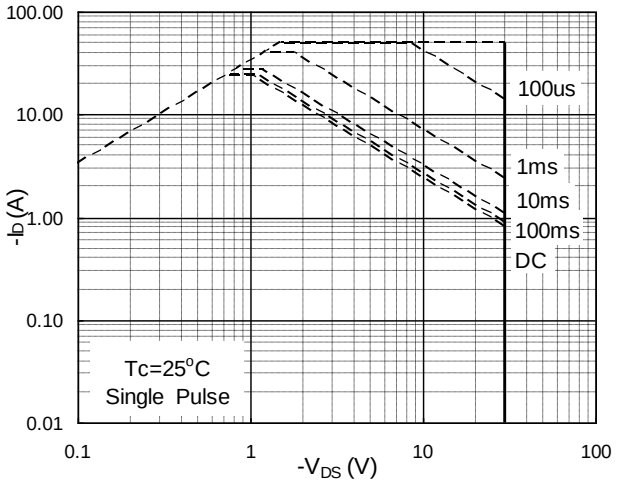
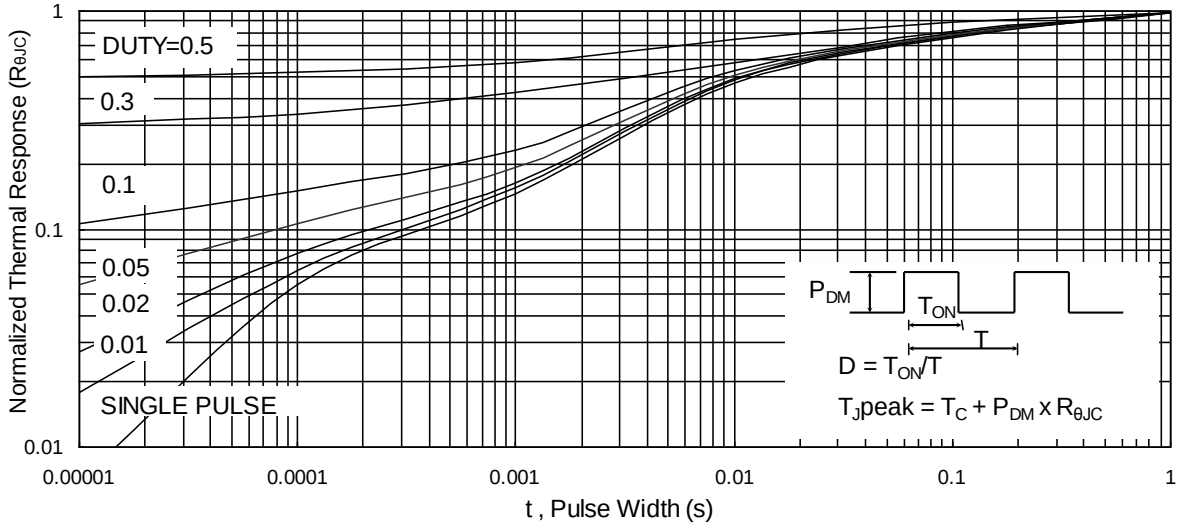


Fig.8 Safe Operating Area



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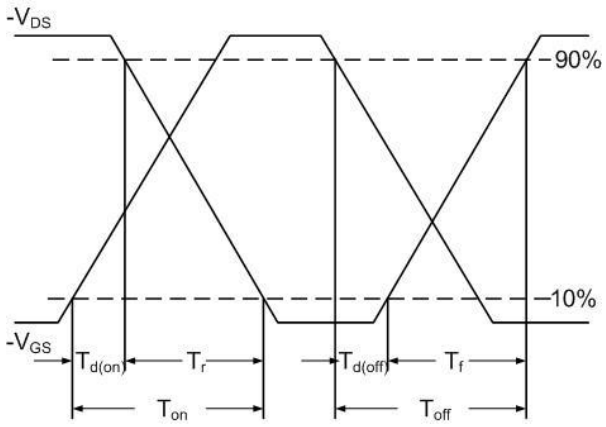


Fig.10 Switching Time Waveform

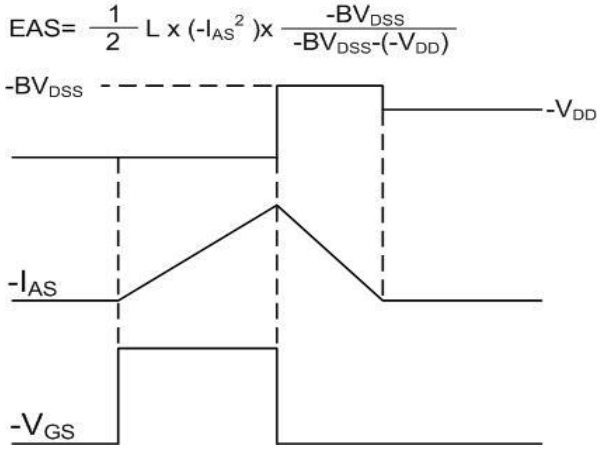
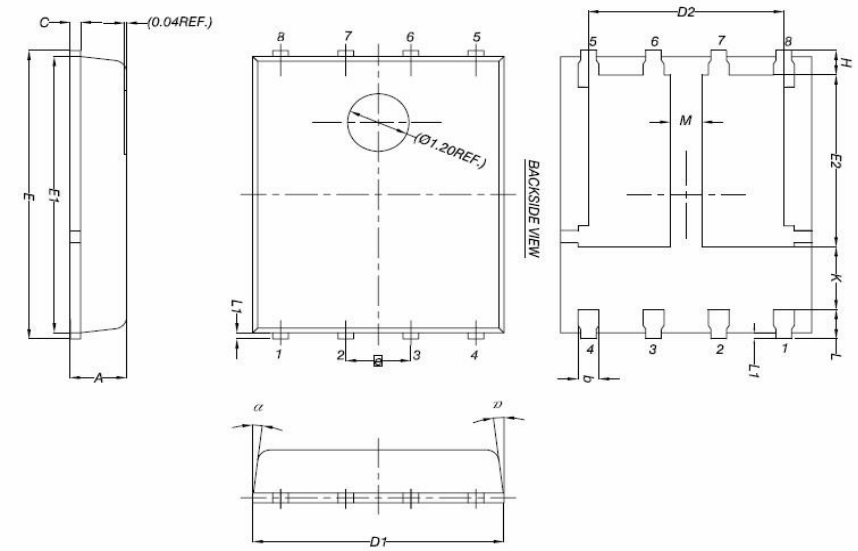


Fig.11 Unclamped Inductive Waveform

Package Mechanical Data-DFN5*6-8L-JQ Double



Symbol	Common		
	mm		
	Mim	Nom	Max
A	0.90	1.00	1.10
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.66	5.76	5.83
E2	3.37	3.47	3.58
e	1.27BSC		
H	0.41	0.51	0.61
K	1.10	--	--
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
M	0.50	--	--
a	0°	--	12°

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Edition	Date	Change
Rve1.0	2020/12/30	Initial release